

Extending Synchronization from Super-threshold to Sub-threshold Region

Jun Zhou, Maryam Ashouei, David Kinniment, Jos Huisken and Gordon Russell**

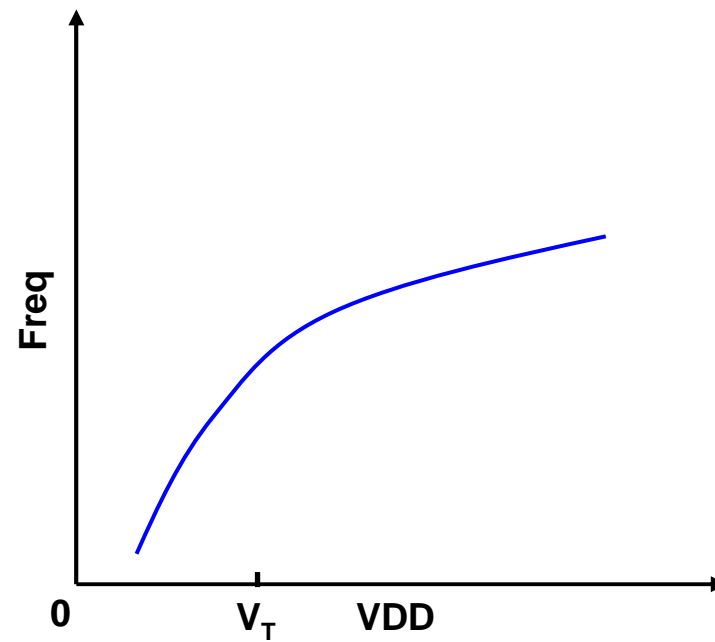
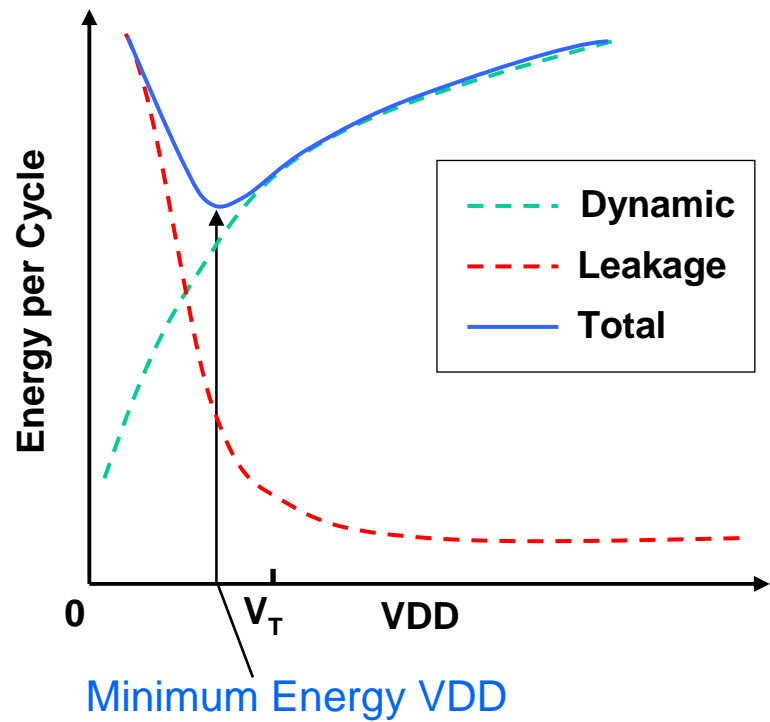
*IMEC Netherlands & *Newcastle University*

- **Sub-threshold Operation**
- **Synchronization in Multi-Low-VDD Systems on Chip**
- **Low Voltage Synchronizer Design**
- **Sub-threshold Synchronizer Design**
- **Results**
- **Implementation**
- **Conclusion**

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Sub-threshold Operation

- **Minimum energy point VDD**
- **Low Performance Requirement**





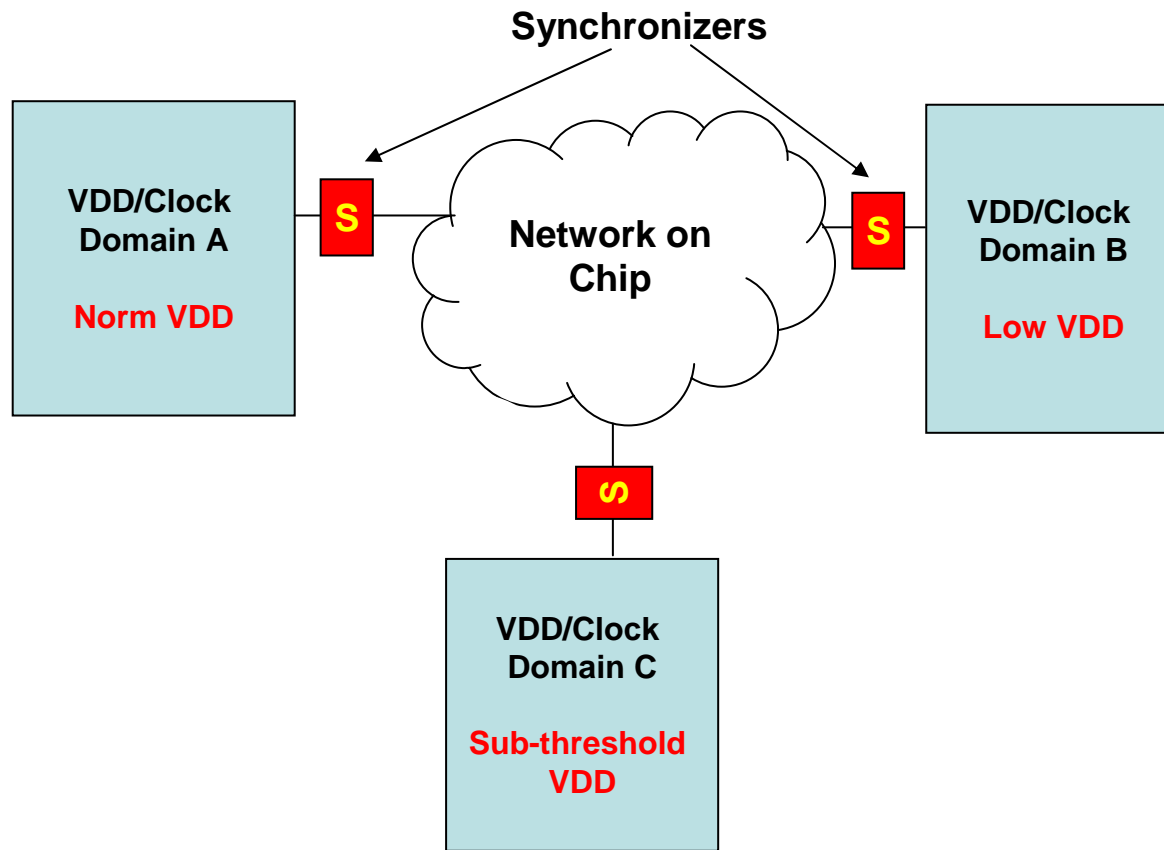
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Multi-Low-VDD Systems on Chip





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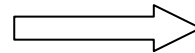
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Synchronizer Performance (MTBF)

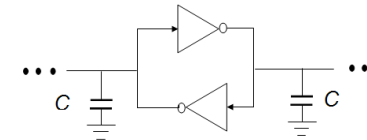
$$MTBF = \frac{e^{\frac{t_s - T_d}{\tau}}}{T_w f_c f_d}$$



t_s : Synchronization Time
 T_d : Normal Propagation Delay
 τ : Metastability Time Constant
 T_w : Metastability Window
 f_c : Clock Frequency
 f_d : Incoming Data Frequency

In the Super-threshold Region:

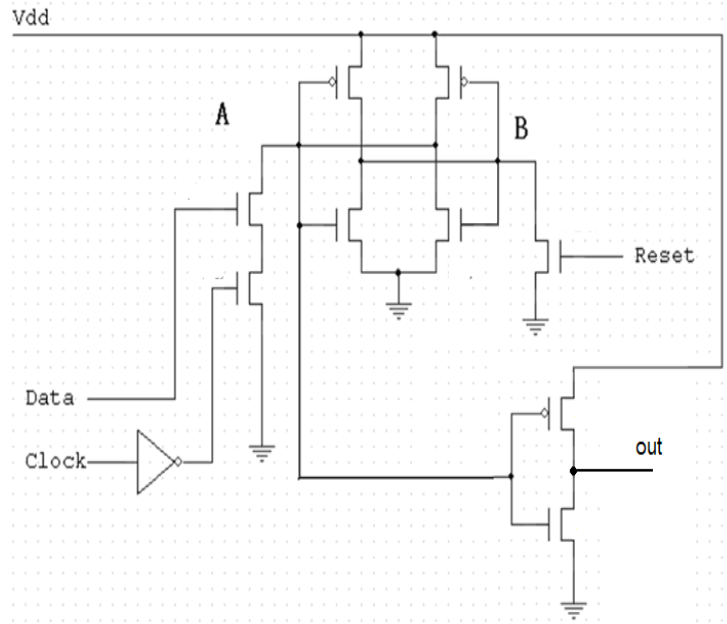
- $T_d \propto VDD$, $VDD \downarrow \rightarrow T_d \uparrow \rightarrow MTBF \downarrow \downarrow$
- $\tau \propto \frac{C}{g_m}$ and $g_m \propto I_d \propto VDD^2$, $VDD \downarrow \rightarrow \tau \uparrow \rightarrow MTBF \downarrow \downarrow$



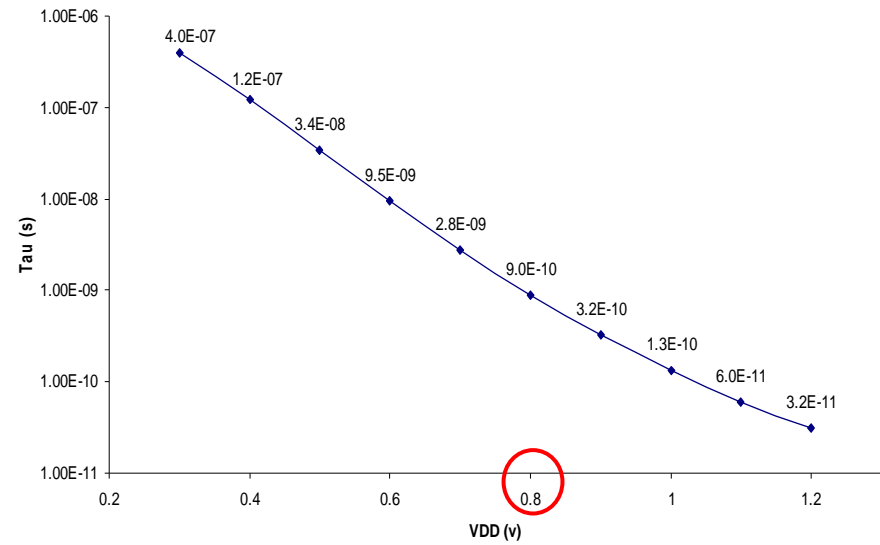
In the Sub-threshold Region:

- $T_d \propto \frac{VDD}{e^{VDD}}$, $VDD \downarrow \rightarrow T_d \uparrow \uparrow \rightarrow MTBF \downarrow \downarrow \downarrow$
- $\tau \propto \frac{C}{g_m}$ and $g_m \propto I_d \propto e^{VDD}$, $VDD \downarrow \rightarrow \tau \uparrow \uparrow \rightarrow MTBF \downarrow \downarrow \downarrow$

Jamb Latch

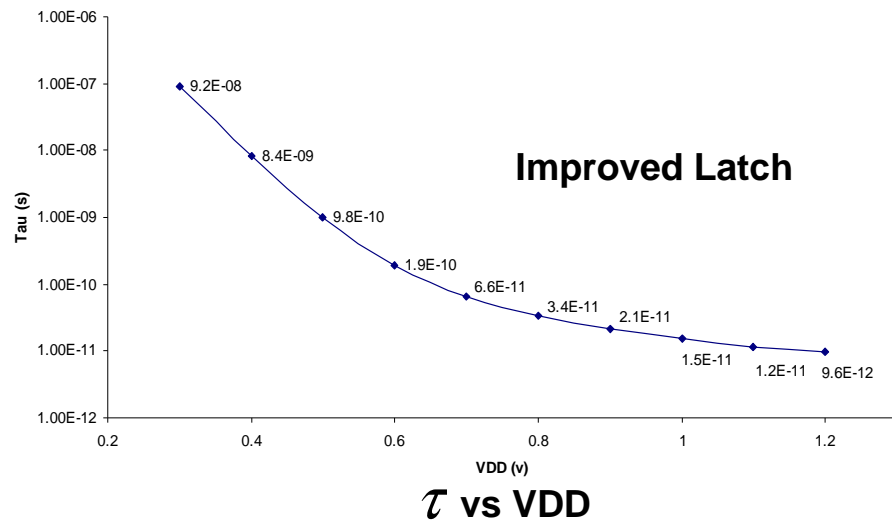
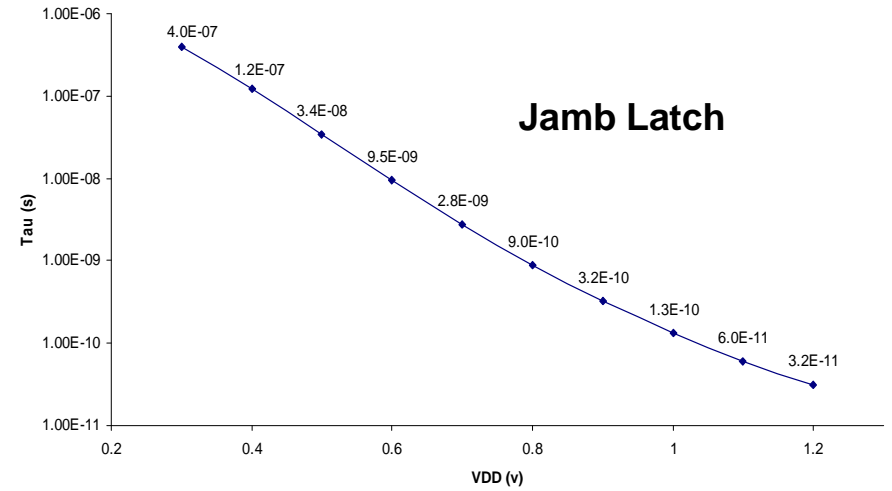
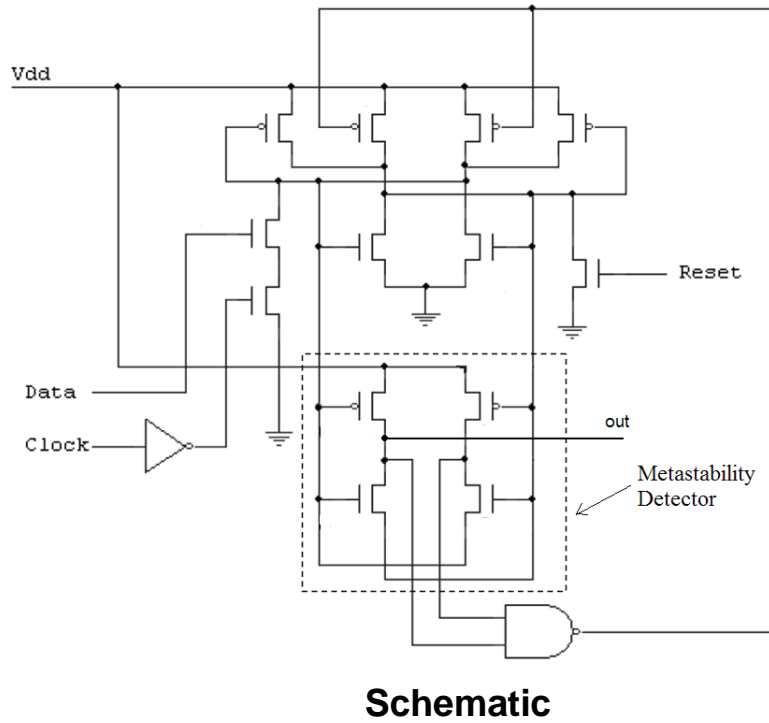


Schematic

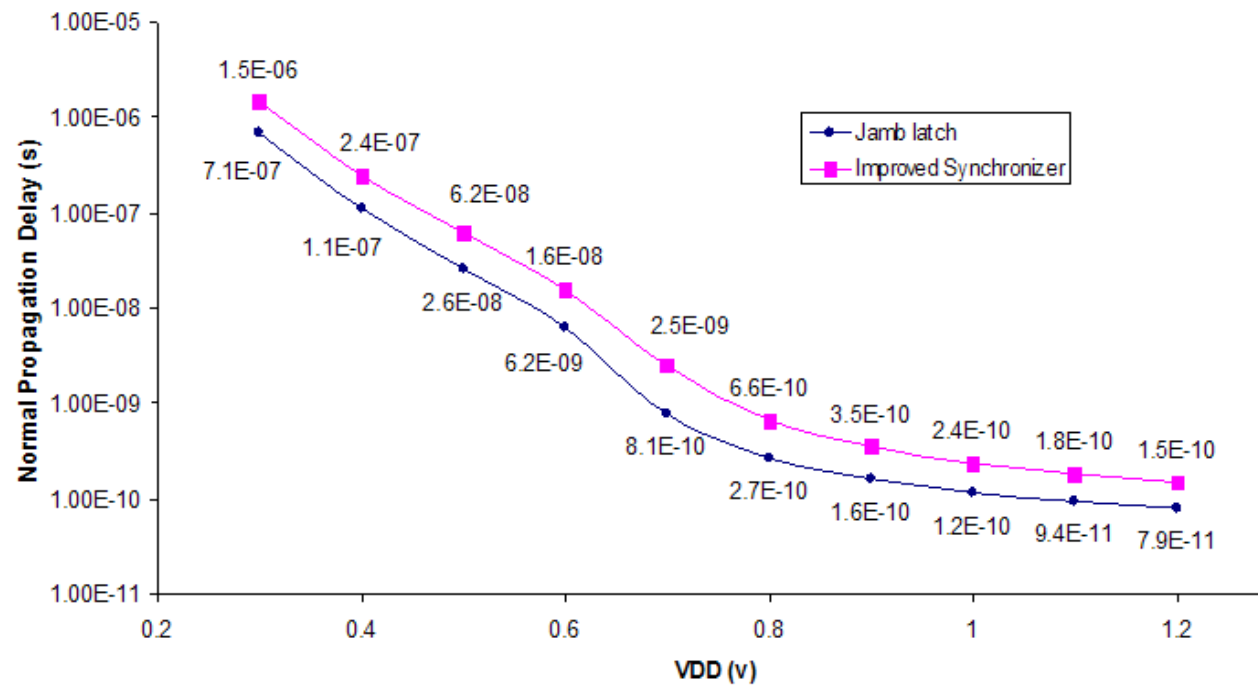


τ vs VDD

Improved Latch



Normal Propagation Delay T_d



Sub-threshold MTBF

$$MTBF = \frac{e^{\frac{t_s - T_d}{\tau}}}{T_w f_c f_d}$$

At 0.3 V, $T_w = 30 \sim 50$ ns. Assuming that $f_c = f_d = 300$ KHz:

	τ	T_d	$MTBF$
Jamb Latch	400 ns	0.7 us	0.17 s
Improved latch	92 ns	1.5 us	2 days

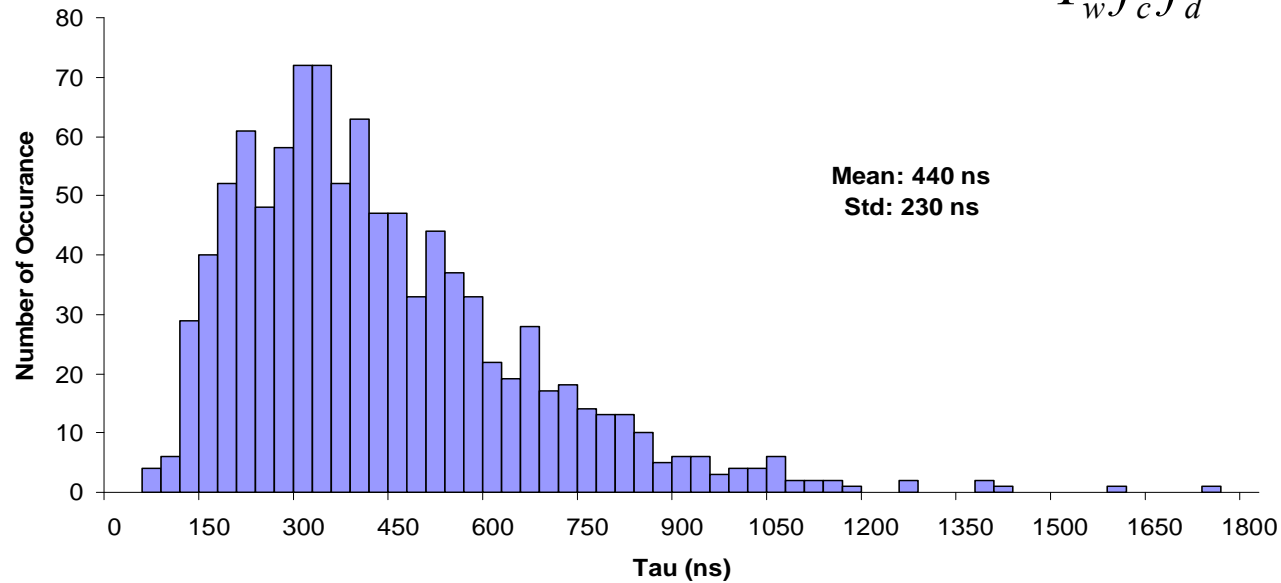
Unacceptable !

Two factors are not taken into account in the calculation:

1. System MTBF = Single MTBF / Num of Synchronizers
2. Large Process Variation in the Sub-Threshold Region

Process Variation

$$MTBF = \frac{e^{\frac{t_s - T_d}{\tau}}}{T_w f_c f_d}$$



Variation of Tau for Jamb Latch at 0.3 V



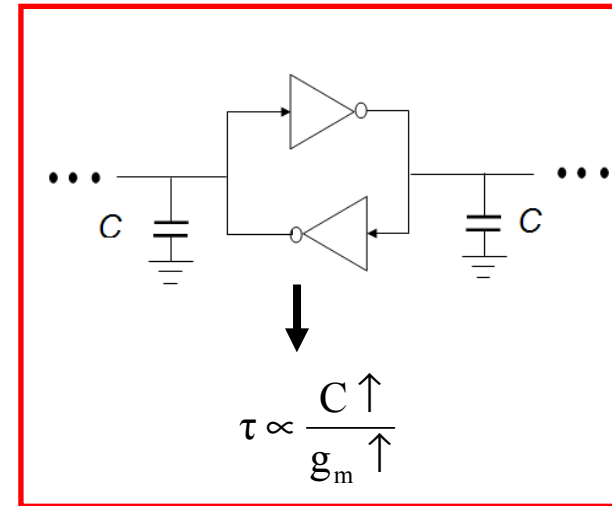
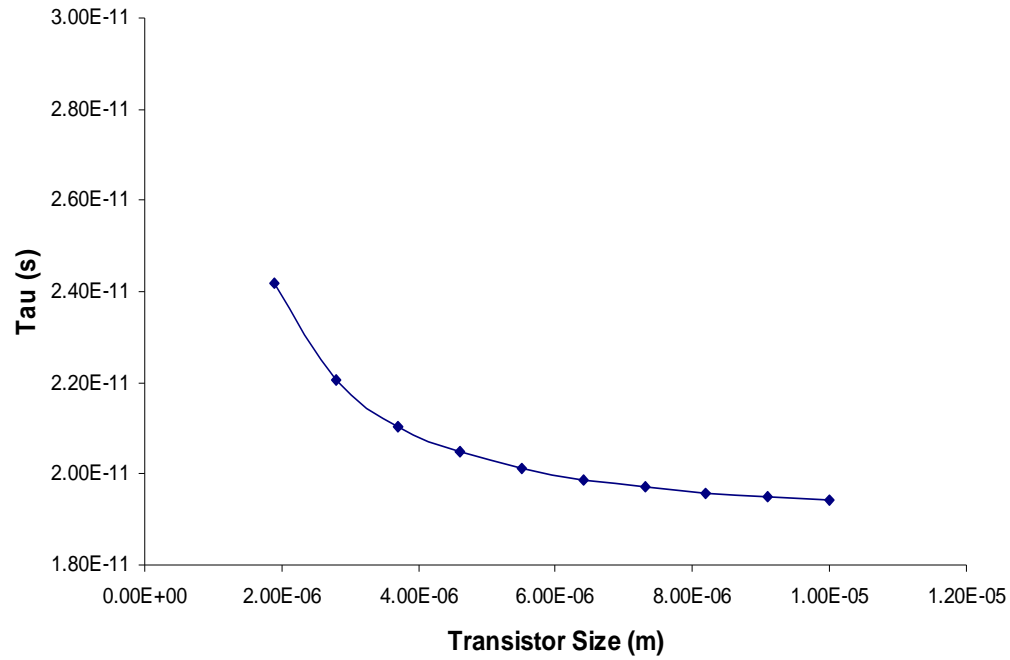
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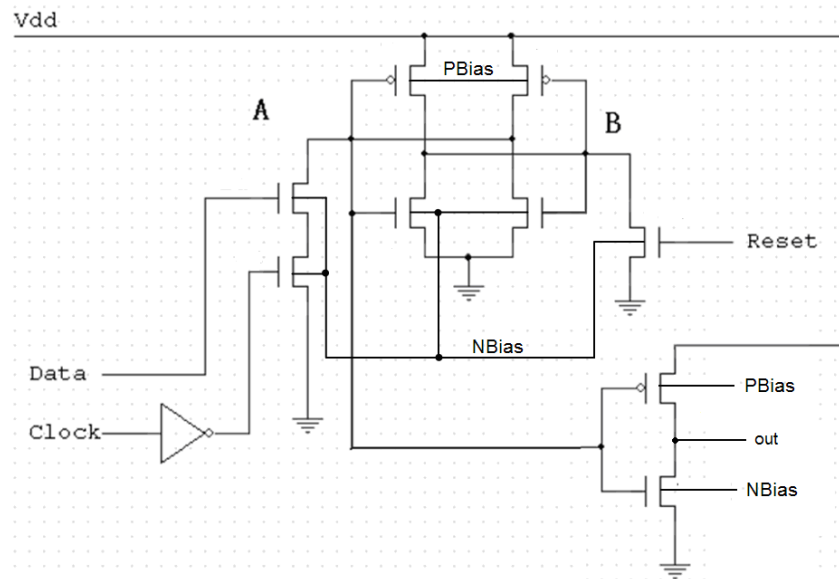
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Increasing Transistor Size?



Applying Forward Body Bias (FBB)



Advantages:

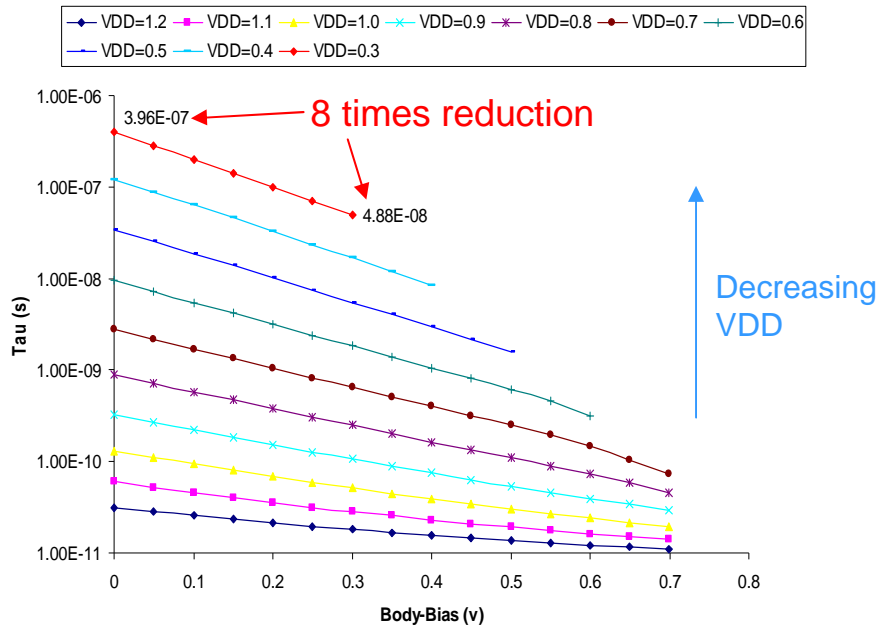
1. Increase g_m without increasing C .
So tau is reduced.
2. Propagation delay is reduced like other logic circuits.
3. Process variation is improved.

Super-threshold: $g_m = \mu_n \cdot C_{ox} \frac{W}{L} \cdot (V_{gs} - V_T)$

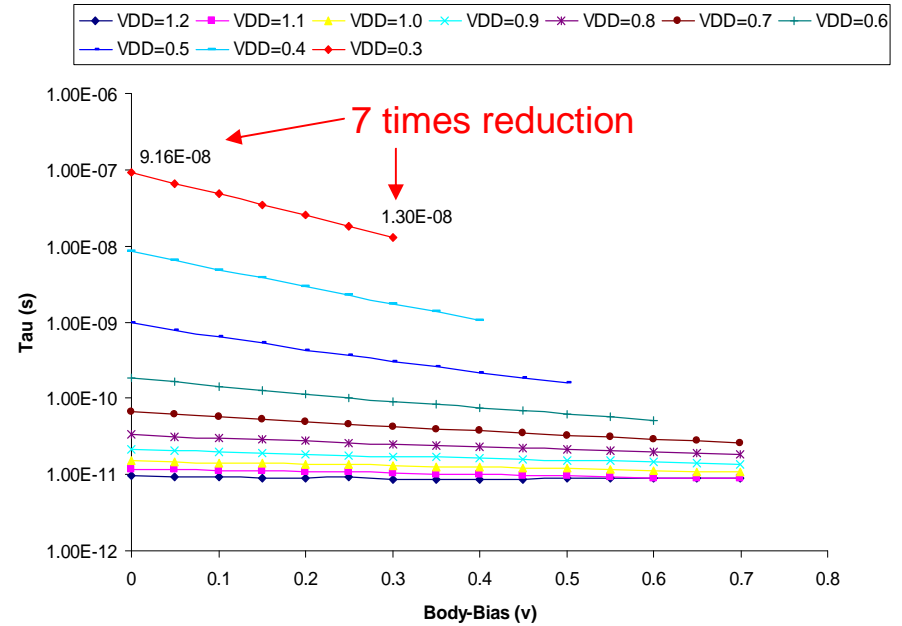
Sub-threshold: $g_m = \frac{I_d}{n \cdot V_{th}}$, $I_d \propto e^{-V_T}$

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Tau vs FBB

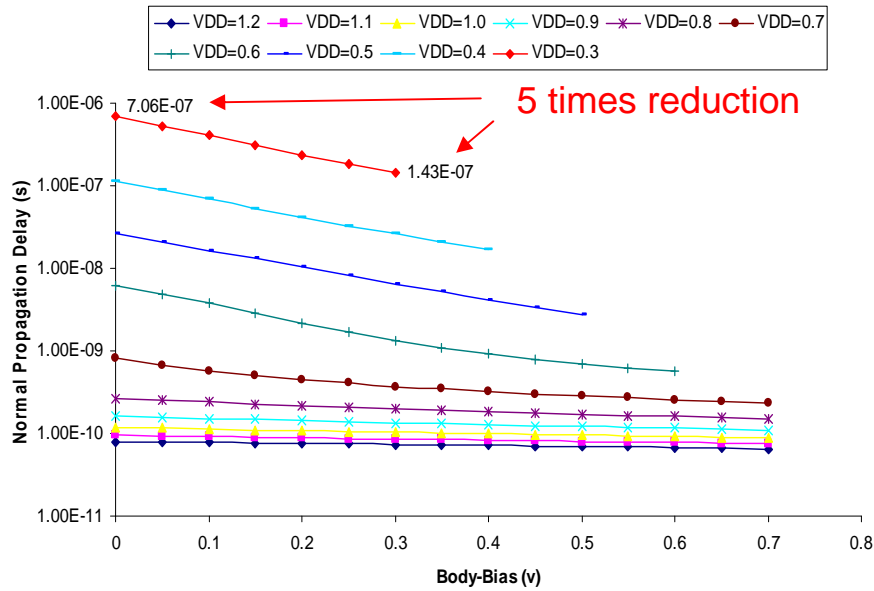


Jamb Latch with FBB

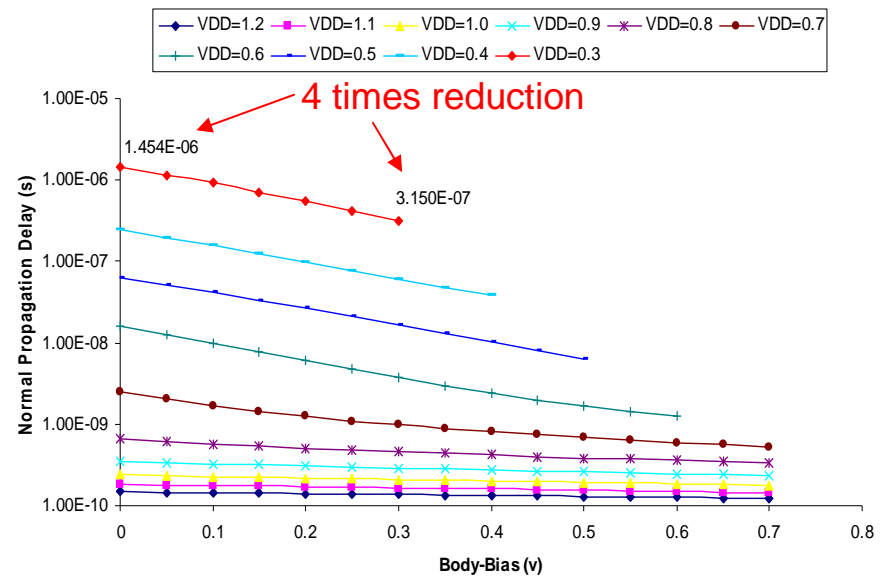


Improved Latch with FBB

Propagation Delay vs FBB

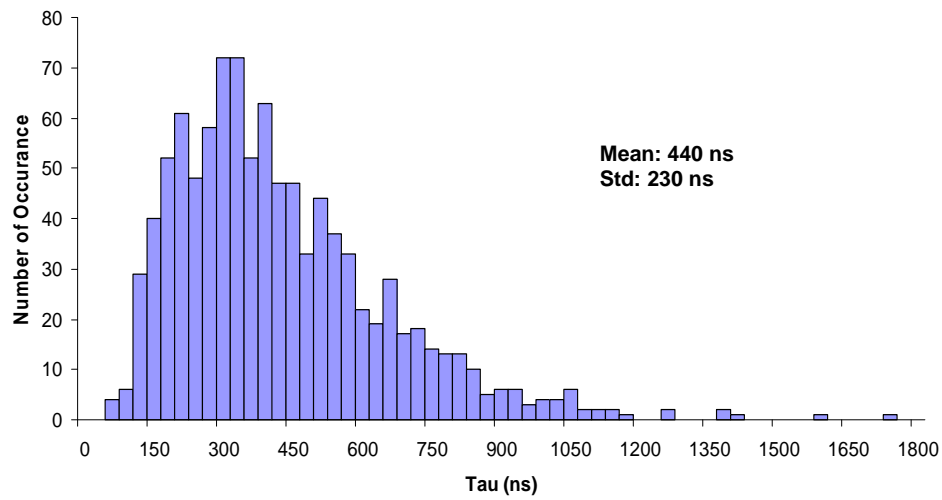


Jamb Latch with FBB

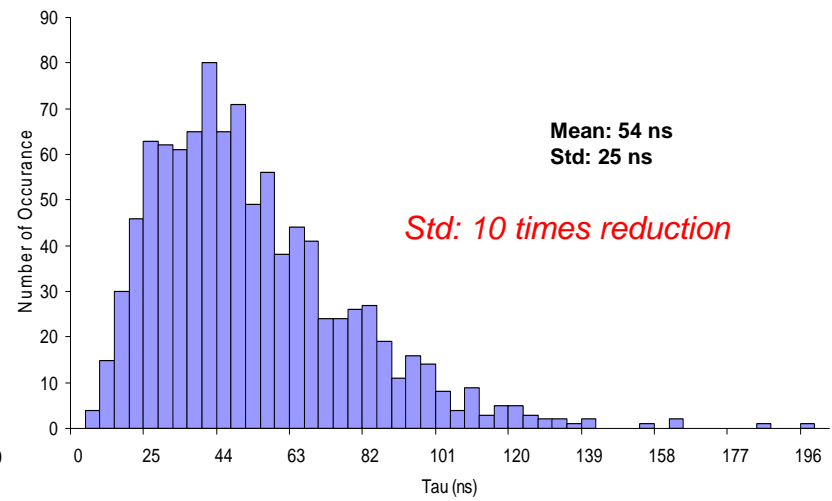


Improved Latch with FBB

Process Variation



Without FBB at 0.3 V



With FBB at 0.3 V

Sub-threshold MTBF

$$MTBF = \frac{e^{\frac{t_s - T_d}{\tau}}}{T_w f_c f_d}$$

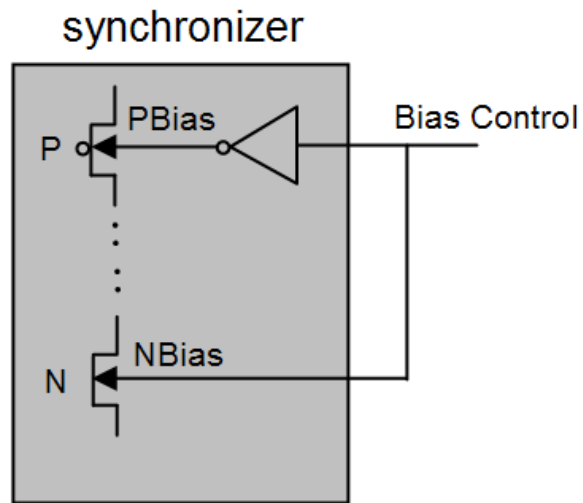
At 0.3 V, $T_w = 7 \sim 15$ ns, assuming that $f_c = f_d = 300$ KHz:

	τ	T_d	<i>MTBF</i>
Jamb Latch	400 ns	0.7 us	0.17 s
Improved latch	92 ns	1.5 us	2 days
Jamb Latch with 0.3V FBB	49 ns	0.14 us	1.35×10^{17} years
Improved Latch with 0.3V FBB	13 ns	0.32 us	4.88×10^{89} years

$3\sigma \rightarrow 4.7$ months

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Full-VDD Biased Synchronizer



Advantage:

- 1. Full-VDD bias gives large performance improvement.*
- 2. No on-chip voltage generation circuit needed (Min Power and Area Overhead).*
- 3. The Bias can be disabled when VDD is higher than the PN junction conducting voltage (0.7 V) to avoid performance degradation.*

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Conclusions

1. For the first time, synchronizer performance is investigated in the near-threshold and sub-threshold region.
2. The investigated synchronizers shows unacceptable MTBF especially when taking into account the process variation.
3. Applying Forward Body Bias significantly improves T_d and τ . It also greatly reduce the impact of process variation on synchronizer performance. As a result, MTBF is significantly improved.
4. A full-VDD biased synchronizer scheme is proposed to improve synchronizer performance in the near-threshold and sub-threshold region with minimal area and power overhead.

Thank you !



Question?